

# PATENT



FORM PTO-1449  <b>INFORMATION DISCLOSURE STATEMENT</b>	<b>ATTY. DOCKET</b> 033035 M 0342	<b>SERIAL NO.</b> 10/691,569
	<b>APPLICANTS:</b> Kensaku MOTOKI, et al.	
	<b>FILING DATE</b> October 24, 2003	<b>GROUP ART UNIT</b> 2814

### U.S. PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE, IF APPROPRIATE
	AA	5,828,088	10/27/1998	MAUK			
	AB	5,838,029	11/17/1998	SHAKUDA			
	AC	5,679,152	10/21/1997	TISCHLER et al.			
	AD	5,182,233	01/26/1993	INOUE			
	AE	5,770,887	06/23/1998	TADATOMO et al.			
	AF						
	AG						

### FOREIGN PATENT DOCUMENTS

*Examiner's Initials		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
							YES	NO
	AH							
	AI							
	AJ							
	AK							

### OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

AL	Office Action for U. S. Patent Application No. 10/691,540 dated April 5, 2005.
AM	IBM, Abstract of "Method of Producing Gallium Nitride Boules for Processing into Substrates," IBM Technical Disclosure Bulletin May 1997, Vol 40, Issue 5, May 1, 1997.
AN	Zheleva et al. "Dislocation density reduction via lateral epitaxy in selectively grown GaN structures," Appl. Phys. Lett. 71 (17) 27 October 1997, pp 2472-2474.
AO	Nam et al. "Lateral epitaxy of low defect density GaN layers via organometallic vapor phase epitaxy," Appl. Phys. Lett. 71 (18), 3 November 1997, pp. 2638-2640.
AP	
AQ	

<b>EXAMINER:</b>	<b>DATE CONSIDERED:</b>
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.